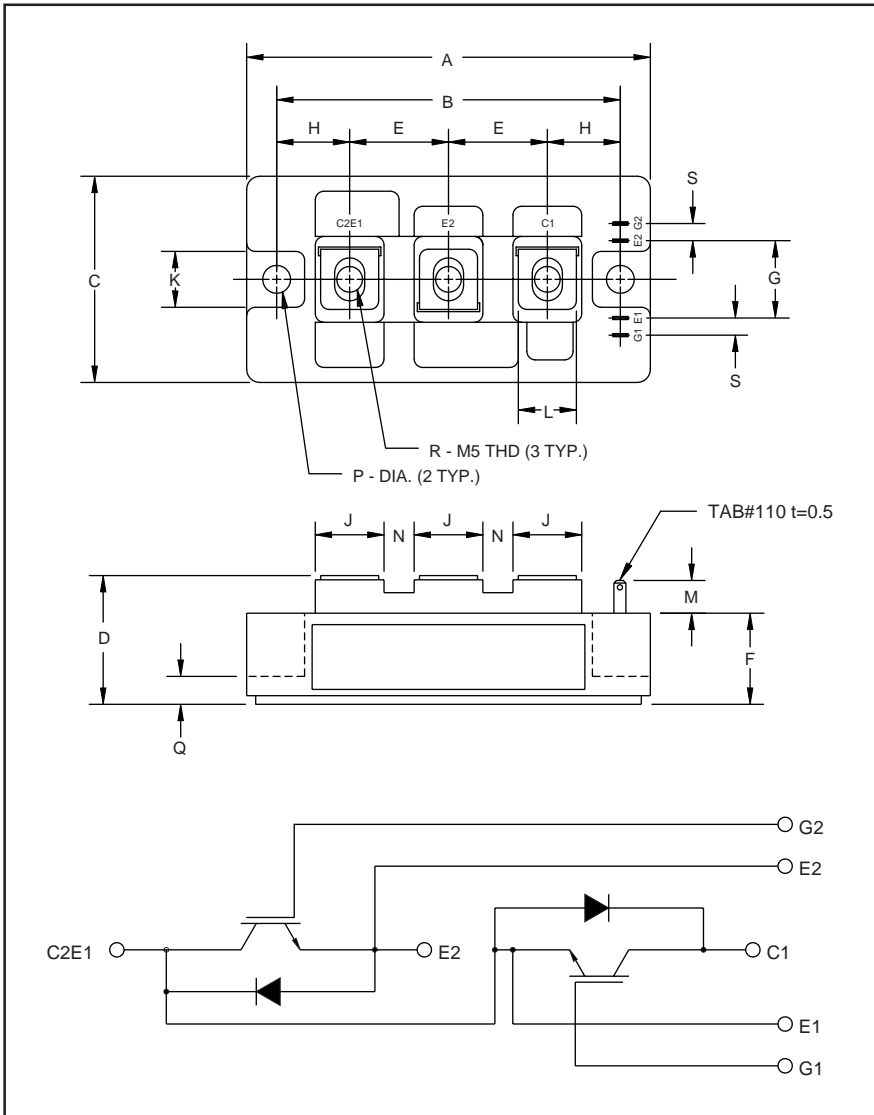


MITSUBISHI IGBT MODULES
CM200DY-12H
 HIGH POWER SWITCHING USE
 INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	3.70	94.0
B	3.150±0.01	80.0±0.25
C	1.89	48.0
D	1.18 Max.	30.0 Max.
E	0.90	23.0
F	0.83	21.2
G	0.71	18.0
H	0.67	17.0
J	0.63	16.0

Dimensions	Inches	Millimeters
K	0.51	13.0
L	0.47	12.0
M	0.30	7.5
N	0.28	7.0
P	0.256 Dia.	Dia. 6.5
Q	0.31	8.0
R	M5 Metric	M5
S	0.16	4.0



Description:

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of two IGBTs in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- High Frequency Operation
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM200DY-12H is a 600V (V_{CES}), 200 Ampere Dual IGBT Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	200	12

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Absolute Maximum Ratings, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

	Symbol	Ratings	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	600	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_C = 25\text{ }^\circ\text{C}$)	I_C	200	Amperes
Peak Collector Current	I_{CM}	400*	Amperes
Emitter Current** ($T_C = 25\text{ }^\circ\text{C}$)	I_E	200	Amperes
Peak Emitter Current**	I_{EM}	400*	Amperes
Maximum Collector Dissipation ($T_C = 25\text{ }^\circ\text{C}$, $T_j \leq 150\text{ }^\circ\text{C}$)	P_c	780	Watts
Mounting Torque, M5 Main Terminal	-	1.47 ~ 1.96	N · m
Mounting Torque, M6 Mounting	-	1.96 ~ 2.94	N · m
Weight	-	270	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Vrms

*Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{\text{CE}} = V_{\text{CES}}$, $V_{\text{GE}} = 0\text{V}$	-	-	1.0	mA
Gate Leakage Current	I_{GES}	$V_{\text{GE}} = V_{\text{GES}}$, $V_{\text{CE}} = 0\text{V}$	-	-	0.5	μA
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_C = 20\text{mA}$, $V_{\text{CE}} = 10\text{V}$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_C = 200\text{A}$, $V_{\text{GE}} = 15\text{V}$	-	2.1	2.8**	Volts
		$I_C = 200\text{A}$, $V_{\text{GE}} = 15\text{V}$, $T_j = 150\text{ }^\circ\text{C}$	-	2.15	-	Volts
Total Gate Charge	Q_G	$V_{\text{CC}} = 300\text{V}$, $I_C = 200\text{A}$, $V_{\text{GE}} = 15\text{V}$	-	600	-	nC
Emitter-Collector Voltage	V_{EC}	$I_E = 200\text{A}$, $V_{\text{GE}} = 0\text{V}$	-	-	2.8	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units	
Input Capacitance	C_{ies}		-	-	20	nF	
Output Capacitance	C_{oes}	$V_{\text{GE}} = 0\text{V}$, $V_{\text{CE}} = 10\text{V}$	-	-	7	nF	
Reverse Transfer Capacitance	C_{res}		-	-	4	nF	
Resistive	Turn-on Delay Time	$V_{\text{CC}} = 300\text{V}$, $I_C = 200\text{A}$, $V_{\text{GE1}} = V_{\text{GE2}} = 15\text{V}$, $R_G = 3.1\Omega$	-	-	200	ns	
Load	Rise Time		t_r	-	-	550	ns
Switching	Turn-off Delay Time		$t_{\text{d(off)}}$	-	-	300	ns
Times	Fall Time		t_f	-	-	300	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 200\text{A}$, $di_E/dt = -400\text{A}/\mu\text{s}$	-	-	110	ns	
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 200\text{A}$, $di_E/dt = -400\text{A}/\mu\text{s}$	-	0.54	-	μC	

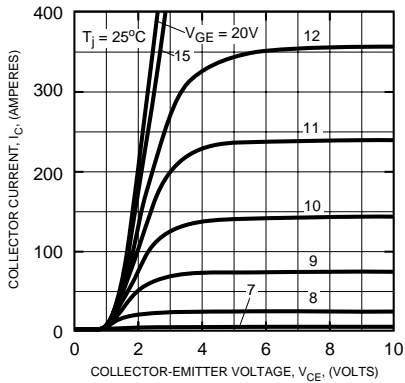
Thermal and Mechanical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per IGBT	-	-	0.16	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per FWDi	-	-	0.35	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{\text{th(c-f)}}$	Per Module, Thermal Grease Applied	-	-	0.065	$^\circ\text{C}/\text{W}$

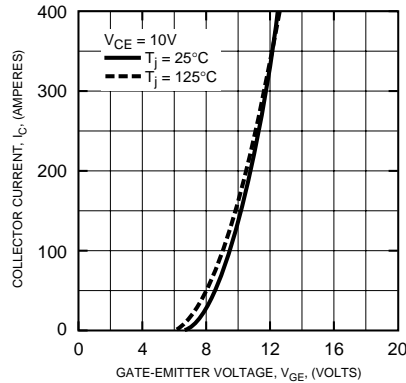
CM200DY-12H

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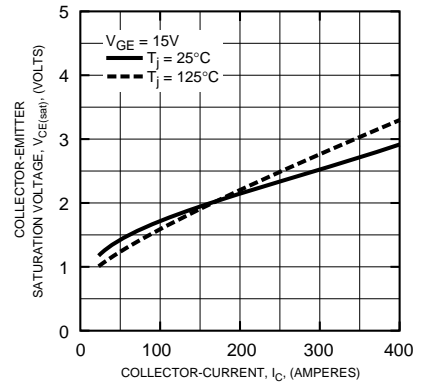
OUTPUT CHARACTERISTICS
(TYPICAL)



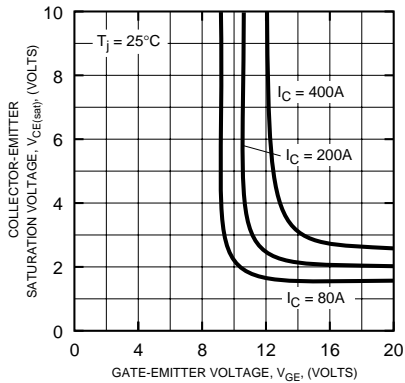
TRANSFER CHARACTERISTICS
(TYPICAL)



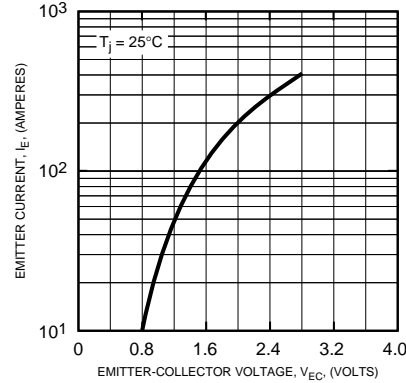
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



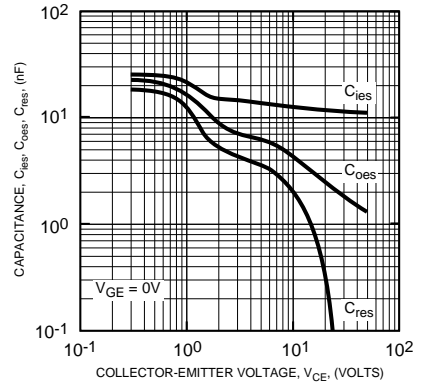
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



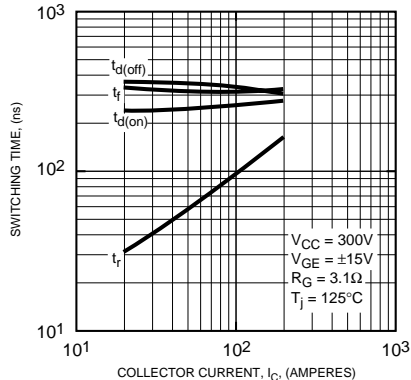
FREE-WHEEL DIODE FORWARD CHARACTERISTICS
(TYPICAL)



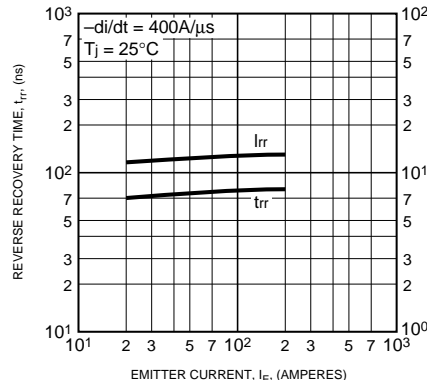
CAPACITANCE VS. V_{CE}
(TYPICAL)



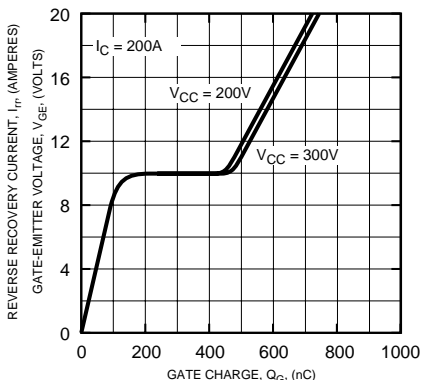
HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE, V_{GE}



CM200DY-12H

HIGH POWER SWITCHING USE
INSULATED TYPE

